

## REMARKS/ARGUMENTS

The title of the invention was objected to.

A new title was provided that overcomes the examiners objection.

Claims 1, 3-5, 7, 8, 15, and 17-20 stand rejected under 35 U.S.C. 103(a) as being unpatentable over Applicants' Admitted Prior Art in view of Hakomori; claims 2 and 16 stand rejected under 35 U.S.C. 103(a) as being unpatentable over Applicants' Admitted Prior Art in view of Hakomori as applied to claims 1 and 15, and further in view of Ang; claim 6 stands rejected under 35 U.S.C. 103(a) as being unpatentable over Applicants' Admitted Prior Art in view of Hakomori as applied to claim 1, and further in view of Ball.

Claim 1 of the instant invention has been amended to include the limitation of forming a SOG layer with a protuberance at the wafer edge. In addition, claim 1 further comprises the limitations of applying a chemical to the spin-on glass protuberance at said outer edge of said semiconductor wafer; and engaging the rotating grinding member with the spin-on glass protuberance at said outer edge of the rotating semiconductor wafer. For references to be combined there must be a suggestion to combine in the references. The Hakomori patent discloses grinding a semiconductor wafer during the formation of the wafer. There is nothing in the Hakomori patent that suggests that such a grinding process can be applied to any additional layer formed on the semiconductor wafer. In addition the Hakomori patent is from the semiconductor wafer manufacture art and the instant invention is in the integrated circuit manufacture art. These are completely different disciplines and there can be no suggestion to combine.

What the examiner refers to as APA simply describes a method of dissolving a portion of the SOG layer. There is nothing in the APA that would suggest that a grinding

process could be used. That disclosure is contained in the description of the instant invention.

Amended claim 1 is therefore allowable over the cited art. Claims 2-8 depend on claim 1 and contain all the limitations of claim 1. Claims 2-8 are therefore also allowable over the cited art.

Claim 15 as amended contains the limitation of forming a SOG layer and grinding the SOG layer immersed in a chemical. These limitations are not found in the cited prior art and claim 15 is allowable over the prior art. Claims 16 – 20 depend on claim 15 and contain the limitations of claim 15. Claims 16 – 20 are therefore also allowable over the cited art.

In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant response places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,



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